

Hall Effect Sensor CY-P3A

CY-P3A Hall Effect Sensor is outstanding for its Ultra-High sensitivity and its low temperature coefficients. This sensor is made by using the technique of Molecular Beam Epitaxy (MBE), which provides excellent uniformity and reproducibility.

Features:

- Ultra-High Sensitivity (380V/AT)
- Low current requirement
- Very low power consumption
- Extended operating temperature range
- Small linearity error of the Hall voltage
- Plastic miniature package SOT-143 for surface mounting
- Wide measuring range (0.1 μ T-2T)



Applications:

- Magnetic field measurement
- Low temperature applications
- Current and power measurement
- Control of brushless DC motors
- Microswitches
- Position sensors

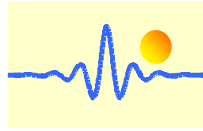
1. Model

CY-P3A Hall Sensor is fabricated from AlGaAs/InGaAs/GaAs-2DEG (two-dimensional electron gas) heterojunction semiconductor.

2. Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
|------------------------------------|-----------|-------------|--------------|
| Control Voltage | V_c | 6 | V |
| Control Current | I_c | 4.5 | mA |
| Power Dissipation | P_D | 26 | mW |
| Operating Temperature | T_{op} | -100 ~ +180 | $^{\circ}$ C |
| Storage Temperature | T_s | -100 ~ +180 | $^{\circ}$ C |
| Soldering Temperature [#] | T_{sol} | 260 | $^{\circ}$ C |

[#]Soldering time: 10 seconds



3. Electrical Characteristics

| Parameter | Symbol | Test Condition | MIN | TYP | MAX | Unit |
|---|--------------|--|-------|-------|-------|---------------------|
| Output Hall Voltage | V_H | $I_c=1\text{mA}$, $B=100\text{mT}$ | - | 38 | - | mV |
| Residual Ratio* ¹ | V_{HO}/V_H | $I_c=1\text{mA}$ | -10 | - | +10 | % |
| Residual Ratio* ¹ | V_{HO}/V_H | $I_c=0.5\text{mA}$ | -4 | - | +4 | % |
| Input Resistance | R_{IN} | $I_c=0.1\text{mA}$, $B=0\text{ mT}$ | 1.28 | 1.3 | 1.35 | k Ω |
| Output Resistance | R_{OUT} | $I_c=0.1\text{mA}$, $B=0\text{ mT}$ | 1.28 | 1.3 | 1.35 | k Ω |
| Temperature Coefficient of Hall Voltage* ² | α | $I_c=1\text{mA}$, $B=100\text{mT}$ ($T_1= -100\text{ }^\circ\text{C}$, $T_2=180\text{ }^\circ\text{C}$) | -0.05 | -0.08 | -0.10 | %/ $^\circ\text{C}$ |
| Temperature Coefficient of Input Resistance* ³ | β | $I_c=1\text{mA}$, $B=0\text{ mT}$ ($T_1= -100\text{ }^\circ\text{C}$, $T_2=180\text{ }^\circ\text{C}$) | - | 0.3 | 0.4 | %/ $^\circ\text{C}$ |
| Linearity of Hall Voltage* ⁴ | γ | $I_c= 1\text{mA}$, $B_1=60\text{mT}$, $B_2=500\text{mT}$ | - | 1 | 1.5 | % |

$$* 1 \quad \text{Residual Ratio} = \frac{V_{HO}(B = 0\text{mT})}{V_H(B = 100\text{mT})}$$

$$* 2 \quad \alpha = \frac{I}{V_H(T_1)} \times \frac{V_H(T_2) - V_H(T_1)}{T_2 - T_1} \times 100$$

$$* 3 \quad \beta = \frac{1}{R_{IN}(T_1)} \times \frac{R_{IN}(T_2) - R_{IN}(T_1)}{T_2 - T_1} \times 100$$

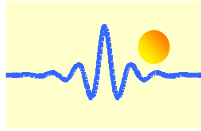
$$* 4 \quad \gamma = \frac{K_H(B_2) - K_H(B_1)}{\frac{1}{2}[K_H(B_2) + K_H(B_1)]} \times 100 \quad K_H = \frac{V_H}{IB}$$

V_{HO} : Offset Voltage

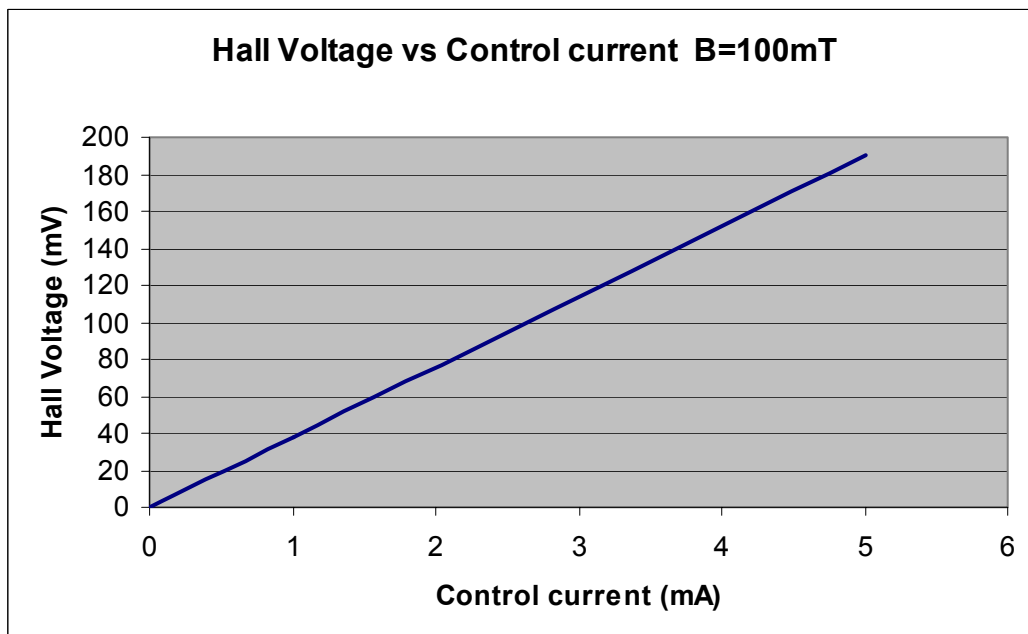
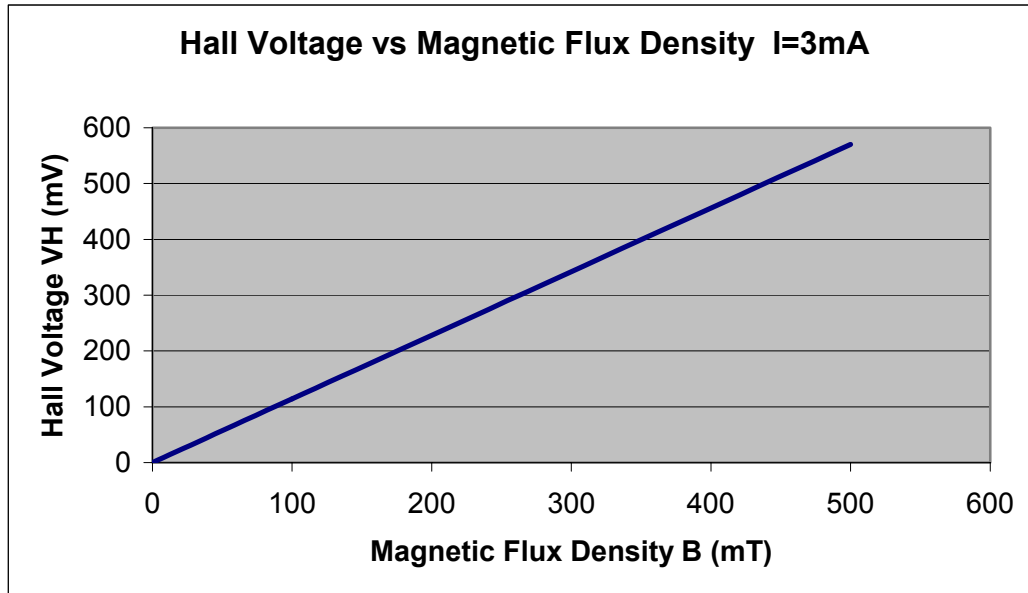
B : Magnetic Flux Density

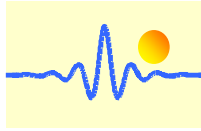
T_1, T_2 : Ambient Temperature

K_H : Current Sensitivity

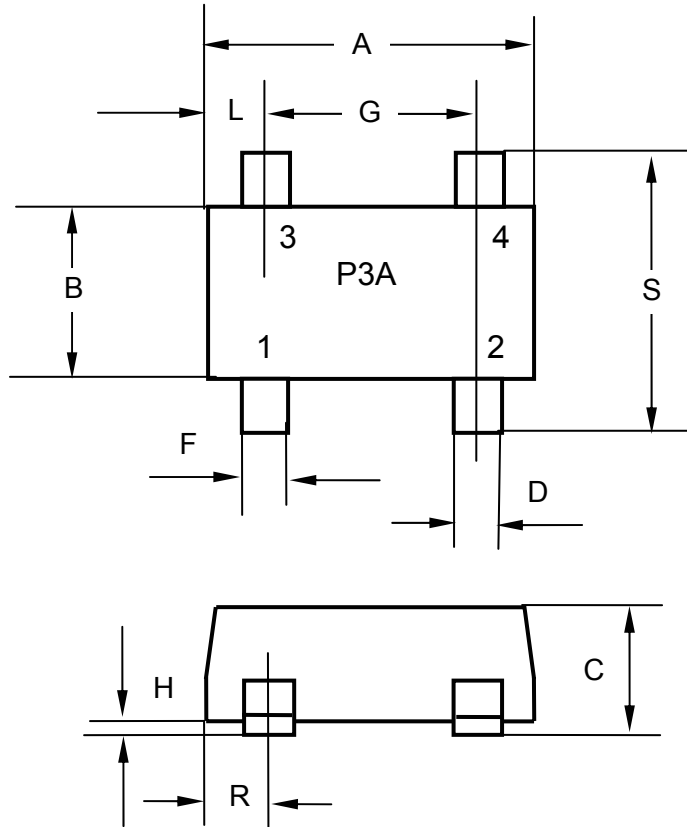


4. Typical Characteristics

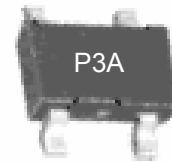




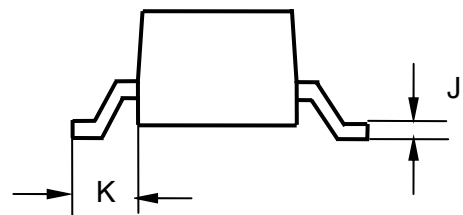
5. Outline drawings (unit: mm)



SOT 143 packaged Hall Sensor



B ↓ Magnetic Field

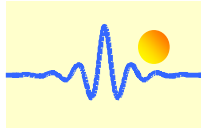


Terminal Connection

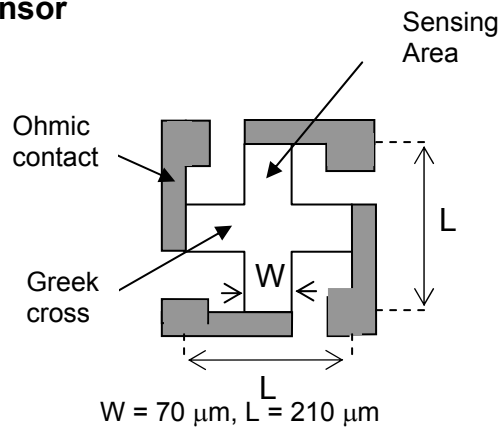
| Terminal No. | | Polarity |
|--------------|--------|----------|
| 1 | Input | (+) |
| 2 | Output | (-) |
| 3 | Output | (+) |
| 4 | Input | (-) |

SOT 143 Package Dimensions

| | Min (mm) | Max (mm) |
|---|----------|----------|
| A | 2.8 | 3.04 |
| B | 1.2 | 1.39 |
| C | 0.89 | 1.14 |
| D | 0.39 | 0.5 |
| F | 0.39 | 0.5 |
| G | 1.78 | 2.03 |
| H | 0.013 | 0.1 |
| J | 0.08 | 0.15 |
| K | 0.46 | 0.6 |
| L | 0.45 | 0.6 |
| R | 0.45 | 0.6 |
| S | 2.11 | 2.48 |



Shape of the 2DEG Hall sensor



Example Circuit

